



SamHop Microelectronics Corp.

STM7822A

Arp,20 2005 ver.1.1

N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DSON} (mΩ) Max
25V	14A	7 @ V _{GS} = 10V
		9 @ V _{GS} = 4.5V

FEATURES

- Super high dense cell design for low R_{DSON}.
- Rugged and reliable.
- Surface Mount Package.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage Rating	V _{spike} ^d	30	V
Drain-Source Voltage	V _{DS}	25	V
Gate-Source Voltage	V _{GS}	±16	V
Drain Current-Continuous ^a @ T _c =25°C -Pulsed ^b	I _D	14	A
	I _{DM}	56	A
Drain-Source Diode Forward Current ^a	I _S	14	A
Maximum Power Dissipation ^a	P _D	2.5	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R _{θJA}	50	°C/W
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ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	25			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=20\text{V}, V_{\text{GS}}=0\text{V}$		1		μA
Gate-Body Leakage	I_{GSS}	$V_{\text{GS}}=\pm 16\text{V}, V_{\text{DS}}=0\text{V}$		± 100		nA
ON CHARACTERISTICS ^b						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	0.7	1.2	2.0	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=14\text{A}$		6	7	m ohm
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=10\text{A}$		8	9	m ohm
On-State Drain Current	$I_{\text{D}(\text{ON})}$	$V_{\text{DS}}=10\text{V}, V_{\text{GS}}=10\text{V}$	10			A
Forward Transconductance	g_{F}	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=14\text{A}$		28		S
DYNAMIC CHARACTERISTICS ^c						
Input Capacitance	C_{ISS}	$V_{\text{DS}}=16\text{V}, V_{\text{GS}}=0\text{V}$ $f=1.0\text{MHz}$		3640		pF
Output Capacitance	C_{OSS}			550		pF
Reverse Transfer Capacitance	C_{RSS}			420		pF
SWITCHING CHARACTERISTICS ^c						
Turn-On Delay Time	$t_{\text{D}(\text{ON})}$	$V_{\text{DD}}=16\text{V},$ $I_{\text{D}}=14\text{A},$ $V_{\text{GS}}=5\text{V},$ $R_{\text{GEN}}=6 \text{ ohm}$		12.3		ns
Rise Time	t_{r}			10.2		ns
Turn-Off Delay Time	$t_{\text{D}(\text{OFF})}$			23.8		ns
Fall Time	t_{f}			12.1		ns
Total Gate Charge	Q_g	$V_{\text{DS}}=16\text{V}, I_{\text{D}}=14\text{A}, V_{\text{GS}}=10\text{V}$		73.9		nC
		$V_{\text{DS}}=16\text{V}, I_{\text{D}}=14\text{A}, V_{\text{GS}}=5\text{V}$		36.2		nC
Gate-Source Charge	Q_{gs}	$V_{\text{DS}}=16\text{V}, I_{\text{D}}=14\text{A},$ $V_{\text{GS}}=5\text{V}$		11.5		nC
Gate-Drain Charge	Q_{gd}			9.9		nC

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ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^b						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0\text{V}$, $I_S = 14\text{A}$		0.84	1.2	V

Notes

- a. Surface Mounted on FR4 Board, $t \leq 10\text{sec}$.
- b. Pulse Test: Pulse Width $\leq 300\text{us}$, Duty Cycle $\leq 2\%$.
- c. Guaranteed by design, not subject to production testing.
- d. Guaranteed when external $R_g=6\text{ ohm}$ and $t_f < t_f \text{ max}$

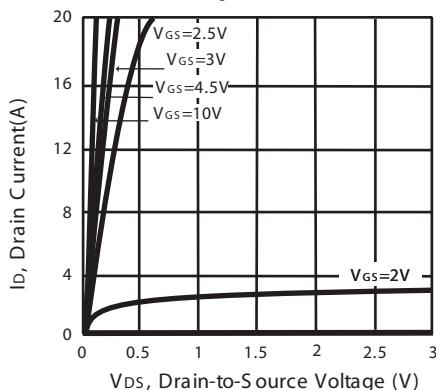


Figure 1. Output Characteristics

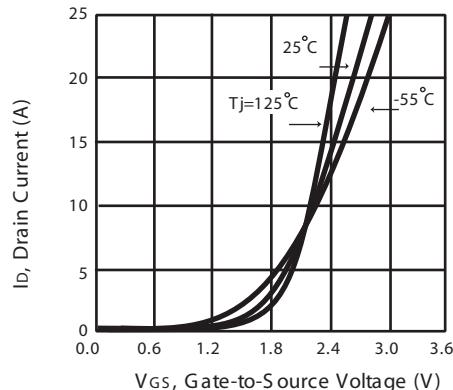


Figure 2. Transfer Characteristics

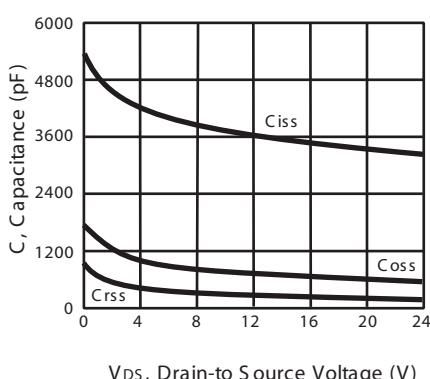


Figure 3. Capacitance

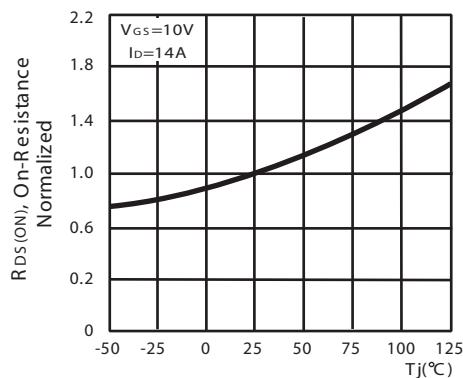
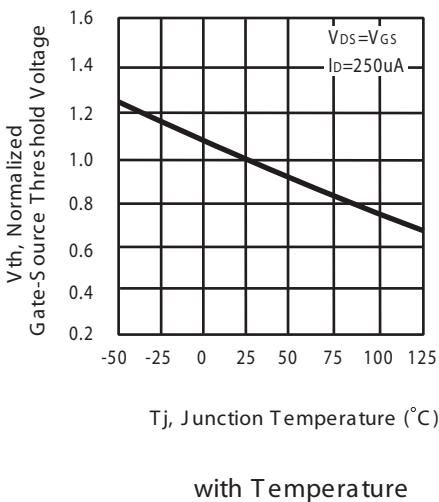


Figure 4. On-Resistance Variation with Temperature

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with Temperature

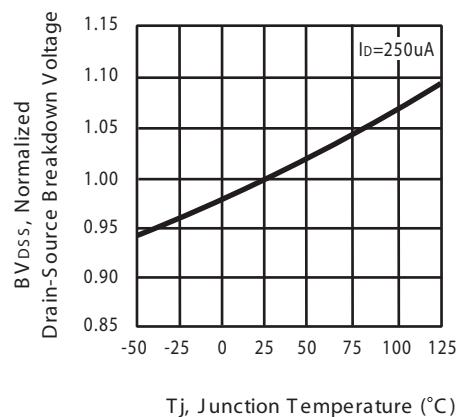
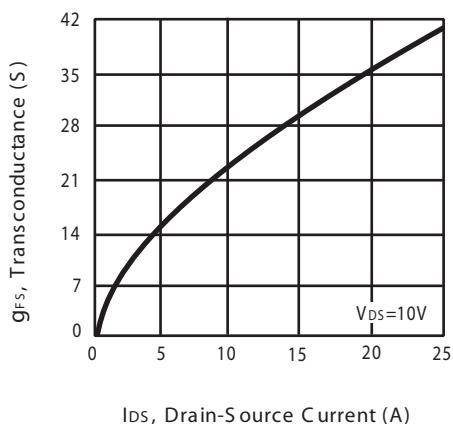
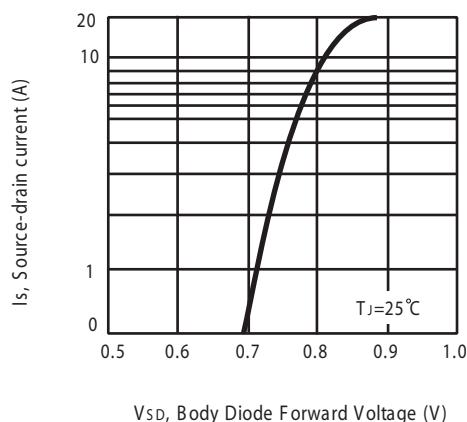


Figure 6. Breakdown Voltage Variation with Temperature



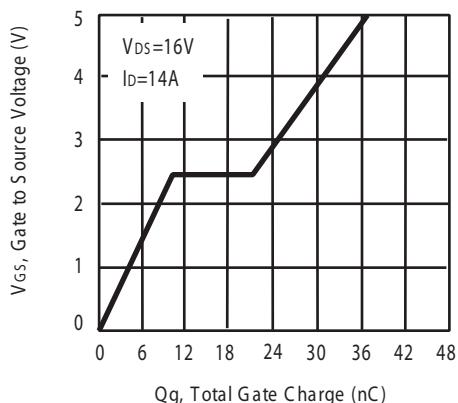
I_{DS} , Drain-Source Current (A)

Figure 7. Transconductance Variation with Drain Current



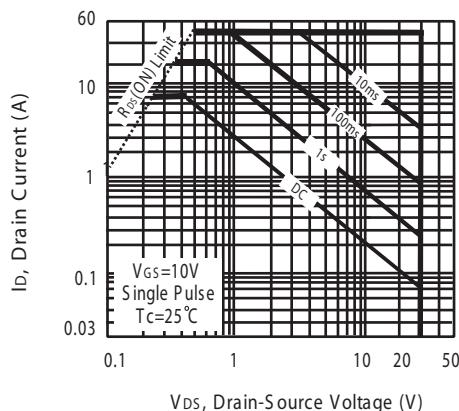
V_{SD} , Body Diode Forward Voltage (V)

Figure 8. Body Diode Forward Voltage Variation with Source Current



Q_g , Total Gate Charge (nC)

Figure 9. Gate Charge



V_{DS} , Drain-Source Voltage (V)

Figure 10. Maximum Safe Operating Area

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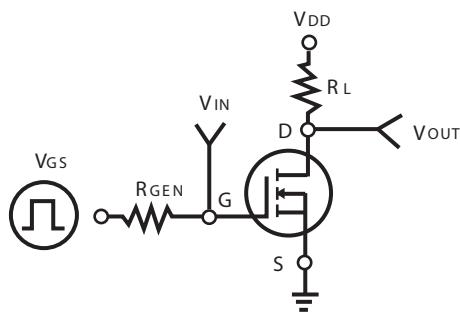


Figure 11. S switching Test Circuit

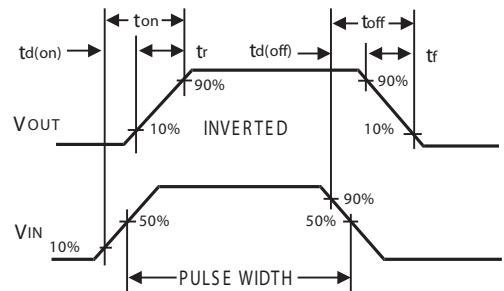


Figure 12. S switching Waveforms

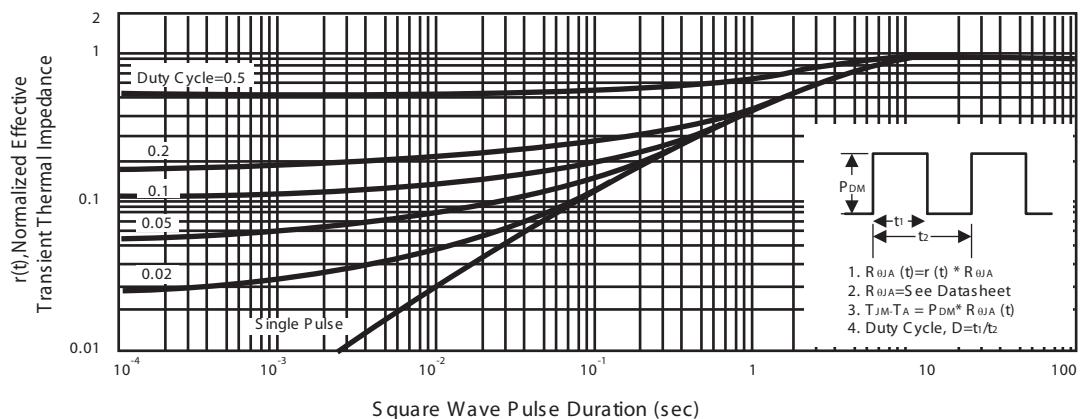
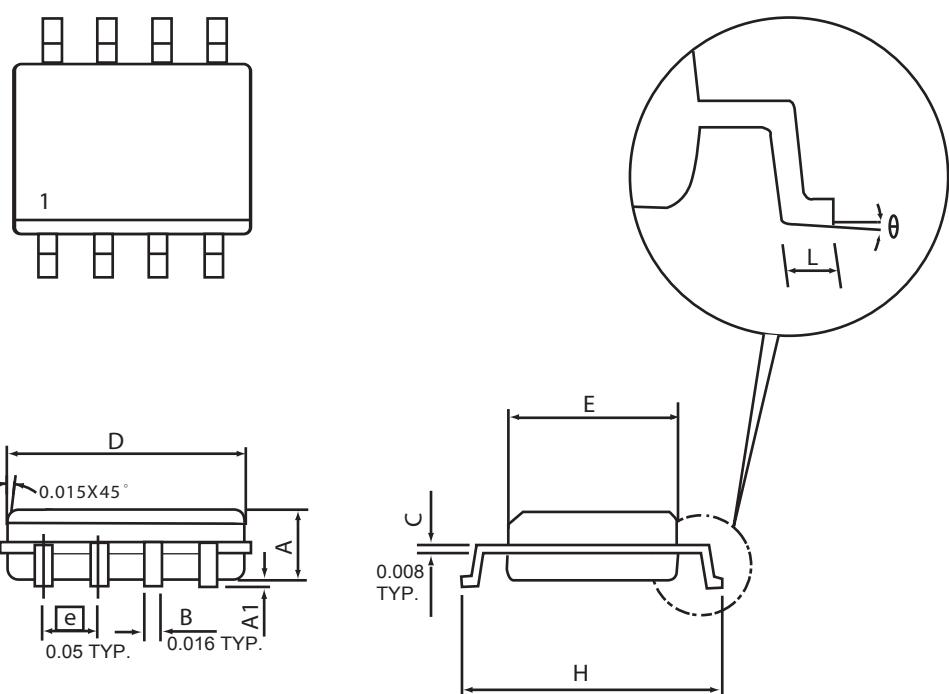


Figure 13. Normalized Thermal Transient Impedance Curve

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PACKAGE OUTLINE DIMENSIONS

SO-8

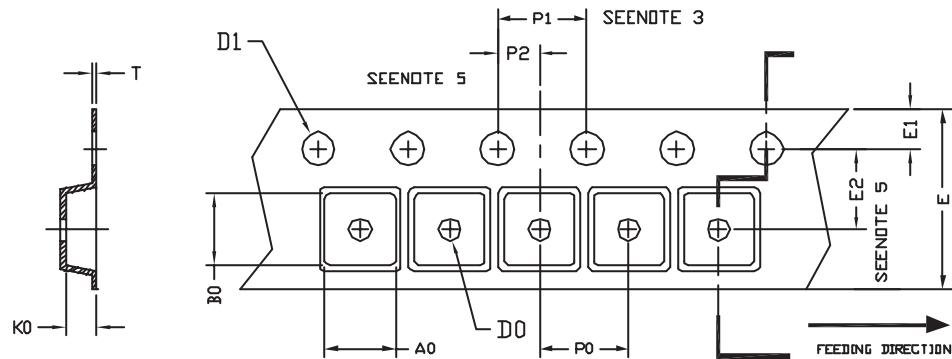


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	4.98	0.189	0.196
E	3.81	3.99	0.150	0.157
H	5.79	6.20	0.228	0.244
L	0.41	1.27	0.016	0.050
θ	0°	8°	0°	8°

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SO-8 Tape and Reel Data

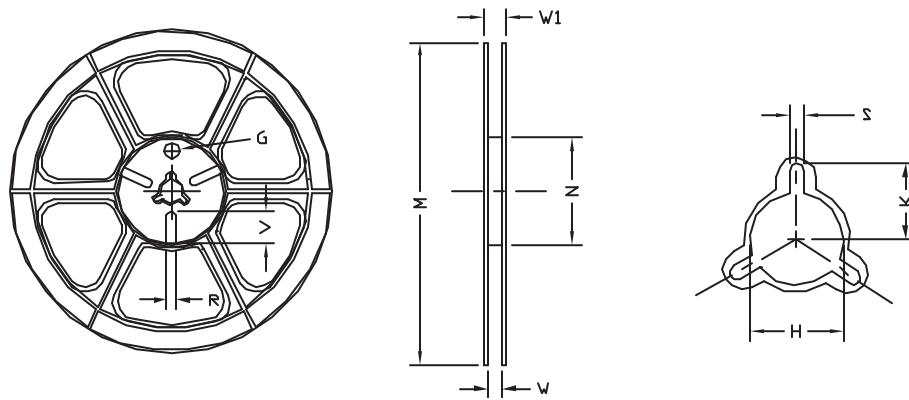
SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.40	5.20	2.10	$\phi 1.5$ (MIN)	$\phi 1.5$ $+ 0.1$ $- 0.0$	12.0 ± 0.3	1.75	5.5 ± 0.05	8.0	4.0	2.0 ± 0.05	0.3 ± 0.05

SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330 ± 1	62 ± 1.5	12.4 $+ 0.2$	16.8 $- 0.4$	$\phi 12.75$ $+ 0.15$	---	2.0 ± 0.15	---	---	---